

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. .... 10/330,881  
Priority Filing Date ..... December 23, 2002  
 Inventor ..... Trung Tri Doan et al.  
 Assignee ..... Micron Technology, Inc.  
Priority Group Art Unit ..... 2813  
Priority Examiner ..... David S. Blum  
 Attorney Docket No. .... MI22-2416  
 Customer No. .... 021567  
 Title ..... Methods of Forming Trench Isolation Regions

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/330,881, filed December 23, 2002. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 10-16-03

By: 

Mark S. Matkin  
Reg. No. 32,268

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTORNEY DOCKET NO.  
MI22-2416PRIORITY SERIAL  
NO. 10/330,881LIST OF ART CITED BY APPLICANT  
(Use several sheets if necessary)

APPLICANT: Trung Tri Doan et al.

PRIORITY FILING DATE  
December 23, 2002PRIORITY GROUP  
ART UNIT 2813

## U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	3,990,927	11/1976	Montier			
	AB	4,474,975	10/1984	Clemons et al.			
	AC	5,156,881	10/1992	Okano et al.			
	AD	5,182,221	01/1993	Sato			
	AE	5,410,176	04/1995	Liou et al.			
	AF	5,470,798	11/1995	Ouellet			
	AG	5,719,085	02/1998	Moon et al.			
	AH	5,741,740	04/1998	Jang et al.			
	AI	5,776,557	07/1998	Okano et al.			

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ	02277253A	11/1990	Japan (Hayashide et al.)				
	AK	146224	01/1996	Japan				
	AL							

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AM		Beekmann et al., <i>Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology</i> , Electrotech 1-7
			ULSI Conference, Portland, OR (October 1995).
	AN		Horie et al., <i>Kinetics and Mechanism of the Reactions of O(<sup>3</sup>P) with SiH<sub>4</sub>, CH<sub>3</sub>SiH<sub>3</sub>, (CH<sub>3</sub>)<sub>2</sub>SiH<sub>2</sub>, and</i>
			<i>(CH<sub>3</sub>)<sub>3</sub>SiH</i> , 95 J. PHYS. CHEM 4393-4400 (1991).
	AO		Joshi et al., <i>Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry</i>
			<i>Mid-Deep UV Photolithography</i> , 1925 SPIE 709-720 (January 1993).
EXAMINER		DATE CONSIDERED	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2416		PRIORITY SERIAL NO. 10/330,881	
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	AB	5,801,083	Yu et al.				
	AC	5,863,827	Joyner				
	AD	5,883,006	Iba				
	AE	5,888,880	Gardner et al.				
	AF	5,895,253	Akram				
	AG	5,904,540	Sheng et al.				
	AH	5,930,645	Lyons et al.				
	AI	5,943,585	May et al.				

  

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AM		Kiermasz et al., <i>Planarisation for Sub-Micron Devices Utilising a New Chemistry</i> , Electrotech 1-2, DUMIC
			Conference, California (February 1995).
	AN		Kojima et al., <i>Planarization Process Using a Multi-Coating of Spin-on-Glass</i> , V-MIC Conference, pp. 390-396
			(June 13-14, 1988).
	AO		Matsuura et al., <i>A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron</i>
			<i>Interconnects</i> , 97 IEEE 785-788 (July 1997).
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	AA	5,950,094	09/1999	Lin et al.			
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	AF	6,051,477	04/2000	Nam			
	AG	6,156,674	12/2000	Li et al.			
	AH	6,300,219 B1	10/2001	Doan et al.			
	AI						

  

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							Yes	No
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	AK							
	AL							

  

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
	AM	Matsuura et al., <i>Novel Self-planarizing CVD Oxide for Interlayer Dielectric Applications</i> , 94 IEEE 117-120 (1994).
	AN	McClatchie et al. <i>Low Dielectric Constant Flowfill™ Technology for IMD Applications</i> , 7 pages (pre-August 1999).
	AO	Withnall et al., <i>Matrix Reactions of Methylsilanes and Oxygen Atoms</i> , 92 J. PHYS. CHEM. 594-602 (1988).
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